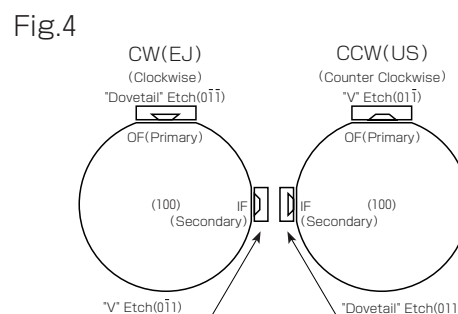
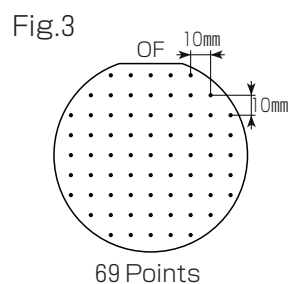
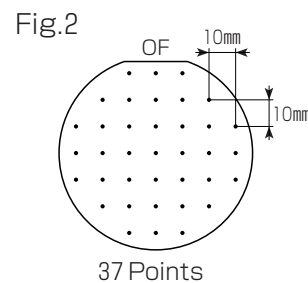
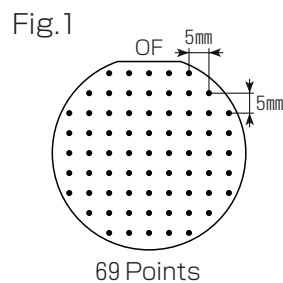


# GaAs Single Crystal Wafers for Laser Diodes

## Standard Specifications

Conduction Type	n-Type			p-Type
	HB·Si	VB·Si		
Growth Method·Dopant	HB·Si	VB·Si		HB·Zn
Carrier Concentration (cm <sup>-3</sup> )	1~4×10 <sup>18</sup>	0.5~4×10 <sup>18</sup>		1~5×10 <sup>19</sup>
Resistivity (Ω·cm)	0.8~3×10 <sup>-3</sup>	1~5×10 <sup>-3</sup>		2.2~8×10 <sup>-3</sup>
Mobility (cm <sup>2</sup> /V·sec)	1.4~2.9×10 <sup>3</sup>	1.2~3×10 <sup>3</sup>		50~90
EPD Average (cm <sup>2</sup> )	≤2×10 <sup>3</sup>	≤5×10 <sup>2</sup>	≤1×10 <sup>2</sup>	≤5×10 <sup>2</sup>
Measuring Points of EPD	Fig.1	Fig.1	Fig.2	Fig.3
Diameter (mm)	50.0±0.3		76.0±0.3	100.0±0.3
OF (mm) (Fig.4)	16.0±2.0		22.0±2.0	32.5±1.0
IF (mm) (Fig.4)	Natural Cleavage			
IF (mm) (Fig.4)	7.0±1.0		12.0±1.0	18.0±1.0
Edge Rounding (mmR)	0.25 (Conform to SEMI Standards)			
Thickness (μm)	350±10	350±10	450±10	350±10
Orientation	(100)±0.3°, (100)2°~15°off±0.3°			(100)±0.3°
Surface Finish	P/LE			
Surface Clean	SC-E (Super Clean Type-E)		SC+ (Super Clean Plus)	SC-E (Super Clean Type-E)
Flatness	Refer to Page 8			
Package	Cassette / Individual Container			



## Attached Data

- Standard : Carrier Concentration · Resistivity · Mobility · Diameter · OF · IF · Thickness (min.~max.)
- Option : Accuracy of Orientation · Flatness · Light Point Defects